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SMD General Purpose Transistor (NPN) BC817-16/BC817-25 ...SMD General Purpose Transistor (NPN) Features • NPN Silicon Epitaxial Planar Transistor For Switching And Amplifier Applications • RoHS Compliance Mechanical Data Case: SOT-23, Plastic Package Terminals: Solderable Per MIL-STD-202G, Method 208 Weight: 0.008 Gram Marking Information BC817-16 BC17-25 BC817-40 Marking Code 6A 6B 6C Apr 10th, 2024 BC817-40W - 45 V, 0.5 A, General Purpose NPN Transistor*Date Code Orientation And/or Overbar May Vary Depending Upon Manufacturing Location. ... Safe Operating Area 1 VCE (Vdc) 0.1 1 0.1 0.01 10 100 0.01 0.001 I C (A) Single Pulse Test @ TA = 25°C Thermal Limit 100 Ms 1 S 10 Ms 1 Ms. SC-70 (SOT-323) CASE 419 ISSUE P DATE 07 OCT 2021 SCALE 4 Feb 20th, 2024 2N4400 & 2N4401 Silicon NPN Transistor General Purpose ...2N4401 40 – 500 Output Admittance H_{oe} IC = 1mA, VCE = 10V, F = 1kHz 1.0 – 30 μ hos Switching Characteristics Delay Time T_d VCC = 30V, VEB = 2V, IC = 150mA, IB1 = 15mA – – 15 Ns Rise Time T_r – – 20 Ns Storage Time T_s VCC = 30V, IC = 150mA, IB1 = IB2 = 15mA – – 225 Ns Fall Time T_f – – 30 Ns Note 1. Pulse Test: Pulse Width \leq ... Mar 9th, 2024.

SMD General Purpose Transistor (PNP) MMBT2907A Marking Code 2F -VCEO Collector-Emitter Voltage (Open Base) 60 V -VCBO Collector-Base Voltage (Open Emitter) 60 V -VEBO Emitter-Base Voltage (Open Collector) 5.0 V -IC Collector Current (D.C) 600 MA P_{tot} Power Dissipation Above 25°C 250 MW FT Transition Frequency At F= 100MHz 200 MHz -IC=50mA, -VCE=20V Jan 6th, 2024 MJE13007 Switch-mode NPN Bipolar Power Transistor Power Transistor For Switching Power Supply Applications The MJE13007 Is Designed For High-voltage, High-speed Power Switching Inductive Circuits Where Fall Time Is Critical. It Is Particularly Suited For 115 And 220 V Switch-mode Applications Such As Switching Regulators, Inverters, Jan 16th, 2024 High Voltage Transistor BF393 NPN Silicon BF393 [Http://onsemi.com](http://onsemi.com) 3 Figure 1. DC Current Gain IC, COLLECTOR CURRENT (mA) 200 1.0 2.0 3.0 5.0 7.0 10 2 Feb 29th, 2024.

Npn Bipolar Junction Transistor EE 436 BJT Currents - 9 External (terminal) Currents. All Currents Depend On V BE In Exactly The Same Way. Although It Is A Messy Exponential, They Are All Tracking Together. It Makes Sense To Look At The Ratios: Forward Current Mar 3th, 2024 MPSA44 NPN High-voltage Transistor NXP Semiconductors Product Data Sheet NPN High-voltage Transistor MPSA44 DATA SHEET STATUS Notes 1. Please Consult The Most Recently Issued Document Before Initiating Or Completing A Design. 2. The Product Status Of Device(s) Described In

This Document May Have Changed Since This Document Was Published And May Differ In Case Of Multiple Devices. Mar 16th, 2024 MJE800/801/802/803 NPN Epitaxial Silicon Darlington Transistor ©2001 Fairchild Semiconductor Corporation Rev. A1, February 2001 MJE800/801/802/803 ... Cross-reference Search Technical Information Buy Products Technical Support My Fairchild Company MJE800 NP Feb 20th, 2024.

2N4401 NPN Switching Transistor - ElectroSchematics.com Jul 02, 2013 · NPN Switching Transistor 2N4401 PACKAGE OUTLINE UNIT A OUTLINE REFERENCES VERSION EUROPEAN PROJECTION ISSUE DATE IEC JEDEC JEITA Mm 5.2 5.0 B 0.48 0.40 C 0.45 0.38 D 4.8 4.4 D 1.7 1.4 E 4.2 3.6 L 14.5 12.7 E 2.54 E1 1.27 L1 (1) Max. 2.5 B1 0.66 0.55 DIMENSIONS (mm Are The Original Dimensions) Note 1. Terminal Dimensions Within This Zone Are ... Jan 20th, 2024 BC546/547/548/549/550 NPN Epitaxial Silicon Transistor Figure 5. Output Capacitance Figure 6. Current Gain Bandwidth Product 0 2468 101214161820 0 20 40 60 80 100 I B = 50µA I B = 100µA I B = 150µA I B = 200µA I B = 250µA I B = 300µA I B = 350µA I B = 400µA I C [mA], COLLECTOR CURRENT V CE [V], COLLECTOR-EMITTER VOLTAGE 0.0 0.2 0.4 0.6 0.8 1.0 1.2 0. Feb 22th, 2024 NTE130 (NPN) & NTE219 (PNP) Silicon Power Transistor ... Silicon Power Transistor Audio Power Amp, Medium Speed Switch Description: The NTE130 (NPN) And NTE219 (PNP) Are Silicon Complementary Transistors In A TO3 Type Case Designed For General Purpose Switching And Amplifier Applications. Features: DC Current Gain: HFE = 20 - 70 @ IC = 4A Collector-Emitter Saturation Voltage: VCE(sat) = 1.1V (Max ... Jan 4th, 2024.

MJE340 - Plastic Medium-Power NPN Silicon Transistor 0.01 0.03 1.0 2.0 5.0 10 20 50 100 2000.1 0.50.2 1.0 0.2 0.1 R(t), Effective Transient 0.05 Jc(t) = R(t) Jc Jc = 3.12°C/w Max D Curves Apply For Power Pulse Train Shown Read Time At T1 ... Asme Y14.5m, 1994. 2. Controlling Dimension: Millimeters. 3. Number And Shape Of Lugs Optional. 2x 2x Q D L1 P B2 B E C L A1 A Front View Back View Front ... Feb 20th, 2024 PBSS4140DPN 40 V Low VCEsat NPN/PNP Transistor 2001 Dec 13 5 NXP Semiconductors Product Data Sheet 40 V Low VCEsat NPN/PNP Transistor PBSS4140DPN Handbook, Halfpage 0 1000 200 400 600 800 MLD642 10-1 1 (1) 10 IC (mA) HFE 102 103 104 Jan 4th, 2024 PBSS4140U 40 V Low VCEsat NPN Transistor - Nexperia 2001 Jul 13 4 NXP Semiconductors Product Data Sheet 40 V Low VCEsat NPN Transistor PBSS4140U Handbook, Halfpage 0 1000 200 400 600 800 MLD660 10-1 1 (1) 10 IC (mA) HFE 102 103 104 Apr 19th, 2024.

NSS20201L - 20 V, 4.0 A, Low VCE(sat), NPN Transistor NSS20201LT1G, NSV20201LT1G Wwww.onsemi.com 2 MAXIMUM RATINGS (TA = 25°C) Rating Symbol Max Unit Collector-Emitter Voltage VCEO 20 Vdc Collector-Base Voltage VCBO 20 Vdc Emitter-Base Voltage VEBO 6.0 Vdc Collector Current – Continuous IC 2.0 A Collector Current – Peak ICM 4.0 A Apr 7th, 2024 NSS12501UW3T2G 12 V, 7.0 A, Low VCE(sat) NPN Transistor Electrostatic Discharge ESD HBM Class 3B MM Class C THERMAL CHARACTERISTICS Characteristic Symbol Max Unit Total Device Dissipation, TA = 25°C Derate Above 25°C PD (Note 1) 875 7.0 MW MW/°C Thermal Resistance, Junction-to-Ambient RJA (Note 1) 143 °C/W Total Device Dissipation, TA Apr 21th, 2024 MPS5179 / MMBT5179 / PN5179 NPN RF Transistor Cover Tape Carrier Tape Note/Comments Packaging Option SOT-23 Packaging Information Standard (no Flow Code) D87Z Packaging Type Reel Size TNR 7" Dia TNR 13" Qty Per

MJE340 - Plastic Medium-Power NPN Silicon Transistor 0.01 0.03 1.0 2.0 5.0 10 20 50 100 2000.1 0.50.2 1.0 0.2 0.1 R(t), Effective Transient 0.05 Jc(t) = R(t) Jc Jc = 3.12°C/w Max D Curves Apply For Power Pulse Train Shown Read Time At T1 ... Asme Y14.5m, 1994. 2. Controlling Dimension: Millimeters. 3. Number And Shape Of Lugs Optional. 2x 2x Q D L1 P B2 B E C L A1 A Front View Back View Front ... Feb 20th, 2024 PBSS4140DPN 40 V Low VCEsat NPN/PNP Transistor 2001 Dec 13 5 NXP Semiconductors Product Data Sheet 40 V Low VCEsat NPN/PNP Transistor PBSS4140DPN Handbook, Halfpage 0 1000 200 400 600 800 MLD642 10-1 1 (1) 10 IC (mA) HFE 102 103 104 Jan 4th, 2024 PBSS4140U 40 V Low VCEsat NPN Transistor - Nexperia 2001 Jul 13 4 NXP Semiconductors Product Data Sheet 40 V Low VCEsat NPN Transistor PBSS4140U Handbook, Halfpage 0 1000 200 400 600 800 MLD660 10-1 1 (1) 10 IC (mA) HFE 102 103 104 Apr 19th, 2024.

NSS20201L - 20 V, 4.0 A, Low VCE(sat), NPN Transistor NSS20201LT1G, NSV20201LT1G Wwww.onsemi.com 2 MAXIMUM RATINGS (TA = 25°C) Rating Symbol Max Unit Collector-Emitter Voltage VCEO 20 Vdc Collector-Base Voltage VCBO 20 Vdc Emitter-Base Voltage VEBO 6.0 Vdc Collector Current – Continuous IC 2.0 A Collector Current – Peak ICM 4.0 A Apr 7th, 2024 NSS12501UW3T2G 12 V, 7.0 A, Low VCE(sat) NPN Transistor Electrostatic Discharge ESD HBM Class 3B MM Class C THERMAL CHARACTERISTICS Characteristic Symbol Max Unit Total Device Dissipation, TA = 25°C Derate Above 25°C PD (Note 1) 875 7.0 MW MW/°C Thermal Resistance, Junction-to-Ambient RJA (Note 1) 143 °C/W Total Device Dissipation, TA Apr 21th, 2024 MPS5179 / MMBT5179 / PN5179 NPN RF Transistor Cover Tape Carrier Tape Note/Comments Packaging Option SOT-23 Packaging Information Standard (no Flow Code) D87Z Packaging Type Reel Size TNR 7" Dia TNR 13" Qty Per

NSS20201L - 20 V, 4.0 A, Low VCE(sat), NPN Transistor NSS20201LT1G, NSV20201LT1G Wwww.onsemi.com 2 MAXIMUM RATINGS (TA = 25°C) Rating Symbol Max Unit Collector-Emitter Voltage VCEO 20 Vdc Collector-Base Voltage VCBO 20 Vdc Emitter-Base Voltage VEBO 6.0 Vdc Collector Current – Continuous IC 2.0 A Collector Current – Peak ICM 4.0 A Apr 7th, 2024 NSS12501UW3T2G 12 V, 7.0 A, Low VCE(sat) NPN Transistor Electrostatic Discharge ESD HBM Class 3B MM Class C THERMAL CHARACTERISTICS Characteristic Symbol Max Unit Total Device Dissipation, TA = 25°C Derate Above 25°C PD (Note 1) 875 7.0 MW MW/°C Thermal Resistance, Junction-to-Ambient RJA (Note 1) 143 °C/W Total Device Dissipation, TA Apr 21th, 2024 MPS5179 / MMBT5179 / PN5179 NPN RF Transistor Cover Tape Carrier Tape Note/Comments Packaging Option SOT-23 Packaging Information Standard (no Flow Code) D87Z Packaging Type Reel Size TNR 7" Dia TNR 13" Qty Per

NSS20201L - 20 V, 4.0 A, Low VCE(sat), NPN Transistor NSS20201LT1G, NSV20201LT1G Wwww.onsemi.com 2 MAXIMUM RATINGS (TA = 25°C) Rating Symbol Max Unit Collector-Emitter Voltage VCEO 20 Vdc Collector-Base Voltage VCBO 20 Vdc Emitter-Base Voltage VEBO 6.0 Vdc Collector Current – Continuous IC 2.0 A Collector Current – Peak ICM 4.0 A Apr 7th, 2024 NSS12501UW3T2G 12 V, 7.0 A, Low VCE(sat) NPN Transistor Electrostatic Discharge ESD HBM Class 3B MM Class C THERMAL CHARACTERISTICS Characteristic Symbol Max Unit Total Device Dissipation, TA = 25°C Derate Above 25°C PD (Note 1) 875 7.0 MW MW/°C Thermal Resistance, Junction-to-Ambient RJA (Note 1) 143 °C/W Total Device Dissipation, TA Apr 21th, 2024 MPS5179 / MMBT5179 / PN5179 NPN RF Transistor Cover Tape Carrier Tape Note/Comments Packaging Option SOT-23 Packaging Information Standard (no Flow Code) D87Z Packaging Type Reel Size TNR 7" Dia TNR 13" Qty Per

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Reel/Tube/Bag 3,000 10,000 Box Dimension (mm) 187x107x183 343x343x64 Max Qty Per Box 24,000 30,000 Weight Per Unit (gm) 0.0082 0.0082 Weight Per Reel (kg) 0.1175 0.4006 Human ... Jan 8th, 2024.

TOSHIBA Transistor Silicon NPN Tr Iple Diffused Type (PCT ...Mar 10, 2010 · Plasma Display, Nixie Tube Driver Applications Cathode Ray Tube Brightness Control Applications • High Breakdown Voltage: VCBO = 300 V, ... 12 14 0.6 2 0.5 0.4 0.3 0.2 50 90 80 12 0 0 10 8 2 80 120 160 Common Emitter Ta = 25°C 70 IB = 10 µA 20 Feb 13th, 20242N4401/MMBT4401 NPN General Purpose Amplifier2N4401 *MMBT4401 PD Total Device Dissipation Derate Above 25°C 625 5.0 350 2.8 MW MW/°C RθJC Thermal Resistance, Junction To Case 83.3 °C/W RθJA Thermal Resistance, Junction To Ambient 200 357 °C/W 2N4401 / MMBT4401 C B E TO-92 C B E SOT-23 Mark: 2X *Device Mounted On FR-4 PCB 1.6" X 1.6" X 0.06." Discrete POWER & Signal Technologies Apr 8th, 2024Small Signal General Purpose Transistors (NPN) 2N4400/2N44012N4400/2N4401 Small Signal General Purpose Transistors (NPN) Www.taitroncomponents.com Page 2 Of 4 Electrical Characteristics (T Ambient=25°C Unless Noted Otherwise) 2N4400 2N4401 Symbol Description Min. Max. Min. Max. Unit Conditions V(BR)CBO Collector-Base Breakdown Voltage 60 - 60 - V IC=100µA, IE=0 Feb 19th, 2024.

2N4401, MMBT4401 - NPN General-Purpose Amplifier2N4401 / MMBT4401 Rev. 1.1.0 November 2014 2N4401 / MMBT4401 NPN General-Purpose Amplifier Ordering Information Figure 1. 2N4401 Device Package Figure 2. MMBT4401 Device Package Part Number Marking Package Packing Method 2N4401BU 2N4401 TO-92 3L Bulk 2N4401TF 2N4401 TO-92 3L Tape And Reel 2N4401TFR 2N4401 TO-92 3L Tape And Reel 2N4401TA 2N4401 ... Mar 13th, 2024LOW FREQUENCY SMD CRYSTALLLOW FREQUENCY SMD ...LOW FREQUENCY SMD CRYSTALLLOW FREQUENCY SMD CRYSTALOW FREQUENCY SMD CRYSTAL STANDARD SPECIFICATIONS: OUTLINE DRAWING: MARKING INSTRUCTIONS: OPTIONS AND PART IDENTIFICATION (Left Blank If Standard): 8.0 X 3.8 X 2.5mm TABLE 1: 20.000 To 27.000 (Fund) 30 9.000 To 12.999 (Fund) 60 13.000 To 15.999 ... Apr 23th, 2024Smd Transistor Code WordpressSize Chart - Footprint Selection Chart - TopLine Dummy 40 V, 200 MA NPN Switching Transistor 5 November 2020 Product Data Sheet 1. General Description NPN Switching Transistor In A Small SOT23 (TO-236AB) Surface-Mounted Feb 8th, 2024.

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